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ON Semiconductor®

# FGA25N120ANTDTU

## 1200 V, 25 A NPT Trench IGBT

### Features

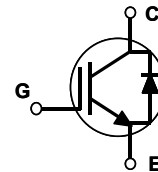
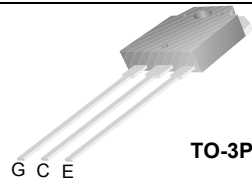
- NPT Trench Technology, Positive Temperature Coefficient
- Low Saturation Voltage:  $V_{CE(sat), typ} = 2.0\text{ V}$   
@  $I_C = 25\text{ A}$  and  $T_C = 25^\circ\text{C}$
- Low Switching Loss:  $E_{off, typ} = 0.96\text{ mJ}$   
@  $I_C = 25\text{ A}$  and  $T_C = 25^\circ\text{C}$
- Extremely Enhanced Avalanche Capability

### Description

Using ON Semiconductor's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device is well suited for the resonant or soft switching application such as induction heating, microwave oven.

### Applications

- Induction Heating, Microwave Oven



### Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
$V_{CES}$	Collector-Emitter Voltage		1200	V
$V_{GES}$	Gate-Emitter Voltage		$\pm 20$	V
$I_C$	Collector Current	@ $T_C = 25^\circ\text{C}$	50	A
	Collector Current	@ $T_C = 100^\circ\text{C}$	25	A
$I_{CM(1)}$	Pulsed Collector Current		90	A
$I_F$	Diode Continuous Forward Current	@ $T_C = 25^\circ\text{C}$	50	A
	Diode Continuous Forward Current	@ $T_C = 100^\circ\text{C}$	25	A
$I_{FM}$	Diode Maximum Forward Current		150	A
$P_D$	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	312	W
	Maximum Power Dissipation	@ $T_C = 100^\circ\text{C}$	125	W
$T_J$	Operating Junction Temperature		-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range		-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	$^\circ\text{C}$

**Notes:**

(1) Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.4	$^\circ\text{C}/\text{W}$
$R_{\theta JC}(\text{DIODE})$	Thermal Resistance, Junction-to-Case	--	2.0	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C}/\text{W}$

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGA25N120ANTDTU-F109	FGA25N120ANTDTU	TO-3PN	Tube	N/A	N/A	30

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

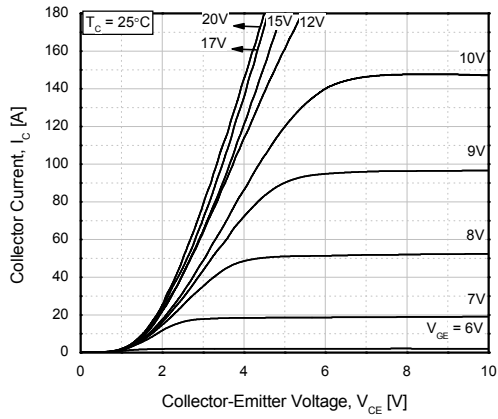
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0 V	--	--	3	mA
I <sub>GES</sub>	G-E Leakage Current	V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0 V	--	--	± 250	nA
<b>On Characteristics</b>						
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 25 mA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	5.5	7.5	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V	--	2.0	--	V
		I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 125°C	--	2.15	--	V
		I <sub>C</sub> = 50 A, V <sub>GE</sub> = 15 V	--	2.65	--	V
<b>Dynamic Characteristics</b>						
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	--	3700	--	pF
C <sub>oes</sub>	Output Capacitance		--	130	--	pF
C <sub>res</sub>	Reverse Transfer Capacitance		--	80	--	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 25°C	--	50	--	ns
t <sub>r</sub>	Rise Time		--	60	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	190	--	ns
t <sub>f</sub>	Fall Time		--	100	--	ns
E <sub>on</sub>	Turn-On Switching Loss		--	4.1	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	0.96	--	mJ
E <sub>ts</sub>	Total Switching Loss		--	5.06	--	mJ
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>CC</sub> = 600 V, I <sub>C</sub> = 25 A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15 V, Inductive Load, T <sub>C</sub> = 125°C	--	50	--	ns
t <sub>r</sub>	Rise Time		--	60	--	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	200	--	ns
t <sub>f</sub>	Fall Time		--	154	--	ns
E <sub>on</sub>	Turn-On Switching Loss		--	4.3	--	mJ
E <sub>off</sub>	Turn-Off Switching Loss		--	1.5	--	mJ
E <sub>ts</sub>	Total Switching Loss		--	5.8	--	mJ
Q <sub>g</sub>	Total Gate Charge	V <sub>CE</sub> = 600 V, I <sub>C</sub> = 25 A, V <sub>GE</sub> = 15 V	--	200	--	nC
Q <sub>ge</sub>	Gate-Emitter Charge		--	15	--	nC
Q <sub>gc</sub>	Gate-Collector Charge		--	100	--	nC

**Electrical Characteristics of DIODE**  $T_C = 25^\circ\text{C}$  unless otherwise noted

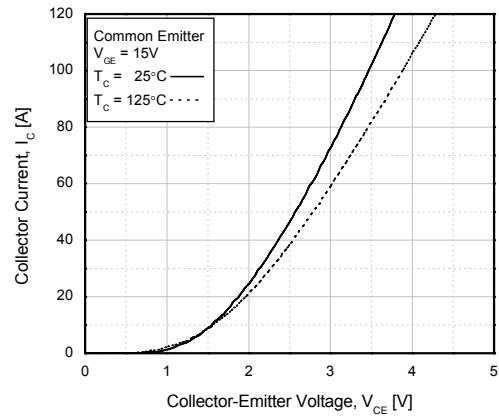
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{FM}$	Diode Forward Voltage	$I_F = 25\text{ A}$	$T_C = 25^\circ\text{C}$	--	2.0	3.0	V
			$T_C = 125^\circ\text{C}$	--	2.1	--	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 25\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	235	350	ns
			$T_C = 125^\circ\text{C}$	--	300	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 25\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	27	40	A
			$T_C = 125^\circ\text{C}$	--	31	--	
$Q_{rr}$	Diode Reverse Recovery Charge	$I_F = 25\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	3130	4700	nC
			$T_C = 125^\circ\text{C}$	--	4650	--	

## Typical Performance Characteristics

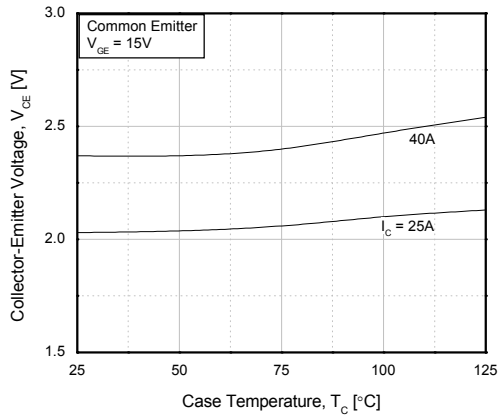
**Figure 1. Typical Output Characteristics**



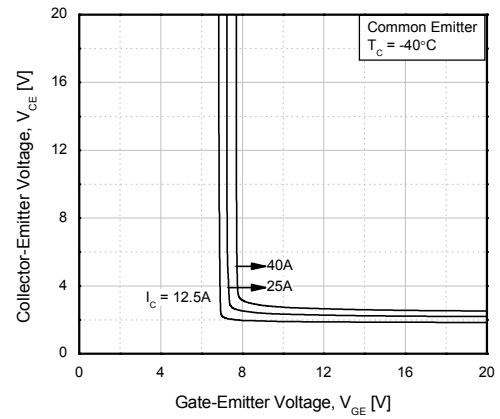
**Figure 2. Typical Saturation Voltage Characteristics**



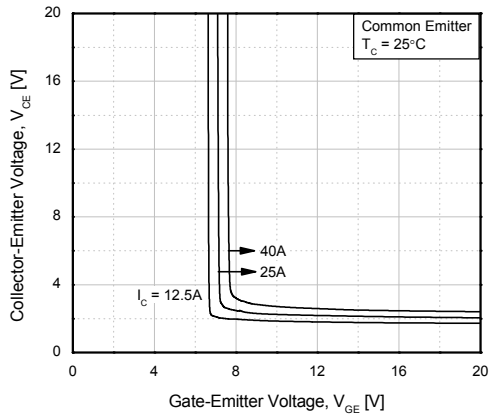
**Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level**



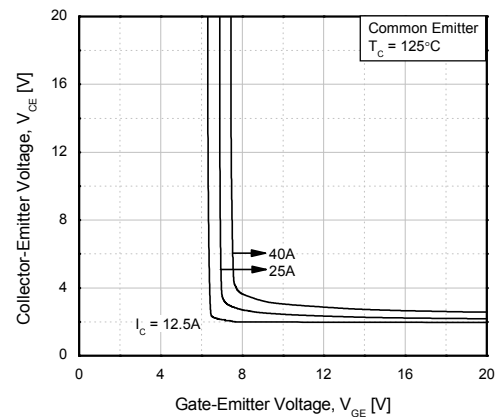
**Figure 4. Saturation Voltage vs. V\_GE**



**Figure 5. Saturation Voltage vs. V\_GE**

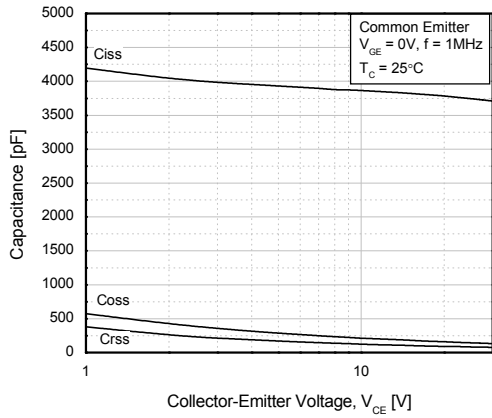


**Figure 6. Saturation Voltage vs. V\_GE**

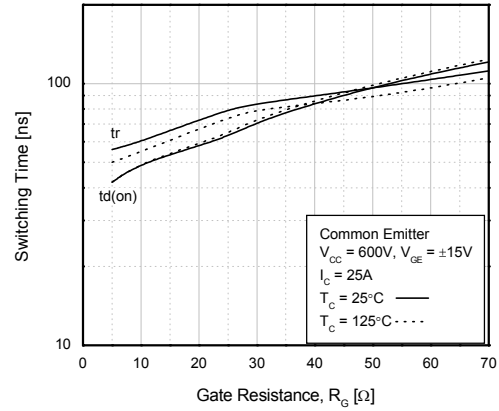


**Typical Performance Characteristics** (Continued)

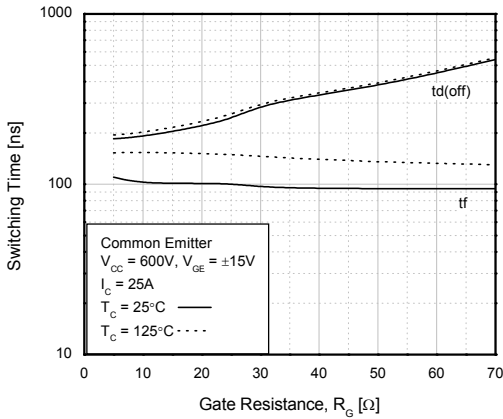
**Figure 7. Capacitance Characteristics**



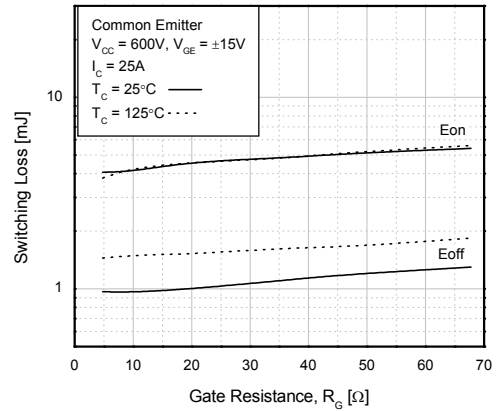
**Figure 8. Turn-On Characteristics vs. Gate Resistance**



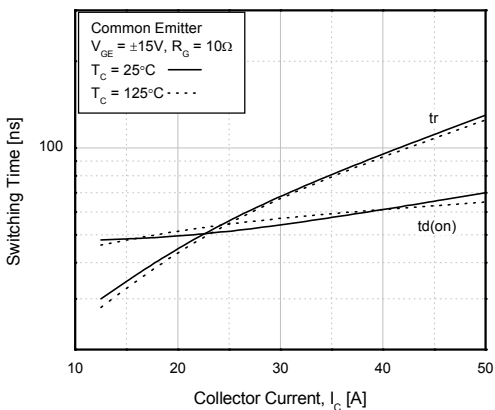
**Figure 9. Turn-Off Characteristics vs. Gate Resistance**



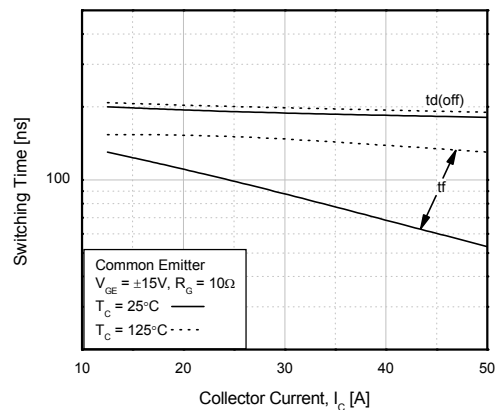
**Figure 10. Switching Loss vs. Gate Resistance**



**Figure 11. Turn-On Characteristics vs. Collector Current**

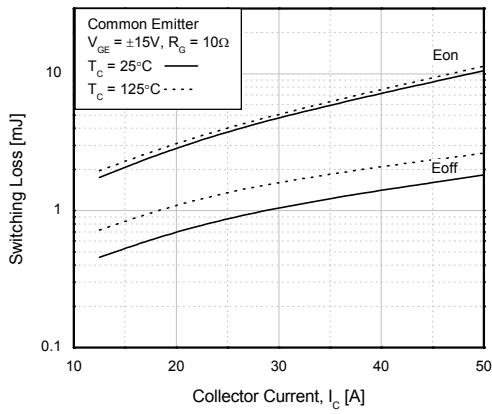


**Figure 12. Turn-Off Characteristics vs. Collector Current**

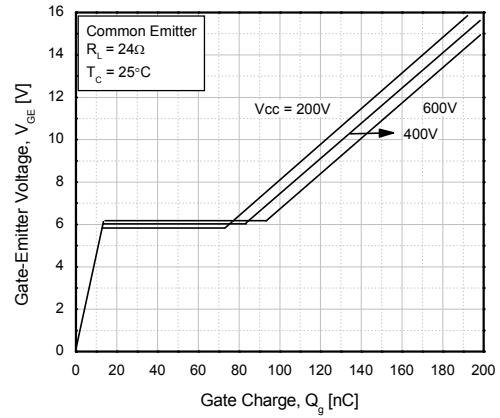


**Typical Performance Characteristics (Continued)**

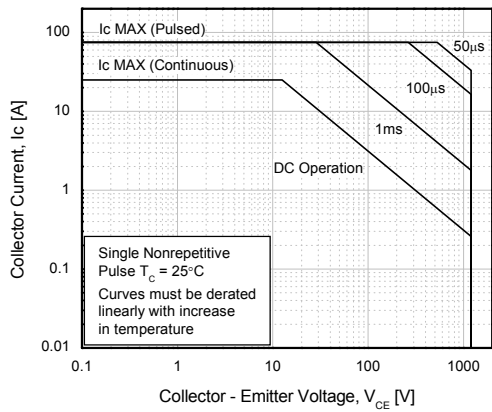
**Figure 13. Switching Loss vs. Collector Current**



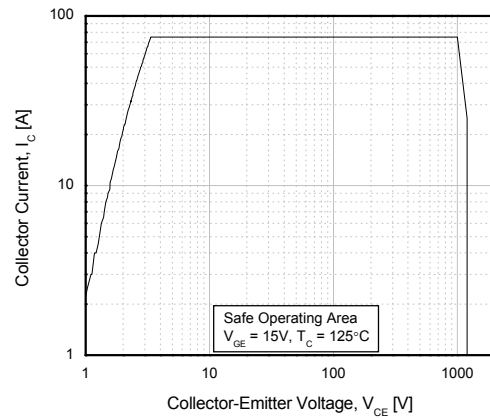
**Figure 14. Gate Charge Characteristics**



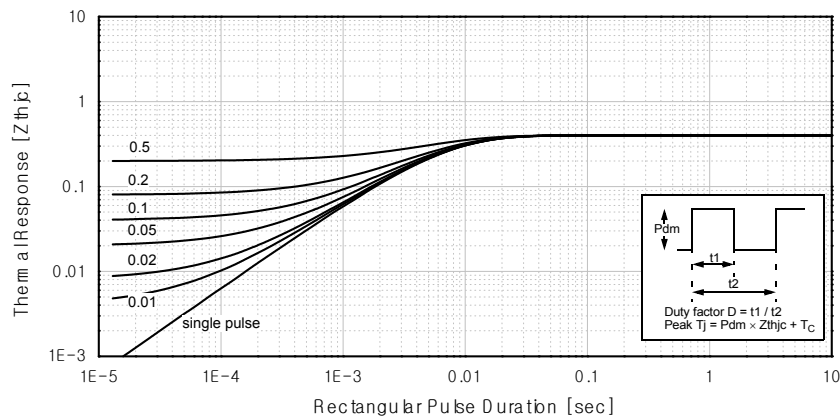
**Figure 15. SOA Characteristics**



**Figure 16. Turn-Off SOA**

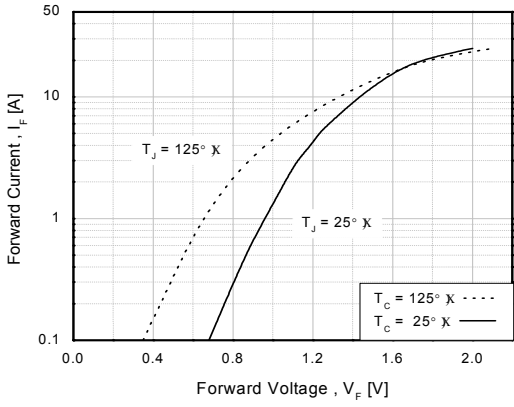


**Figure 17. Transient Thermal Impedance of IGBT**

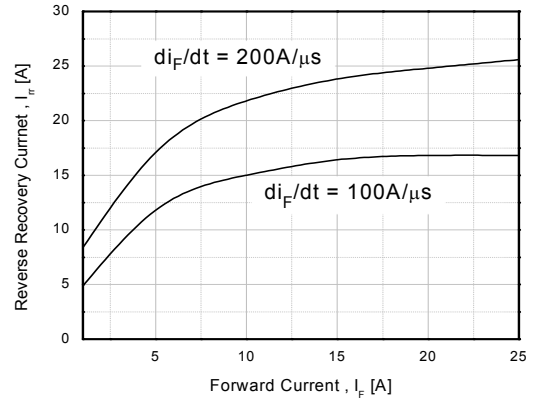


**Typical Performance Characteristics** (Continued)

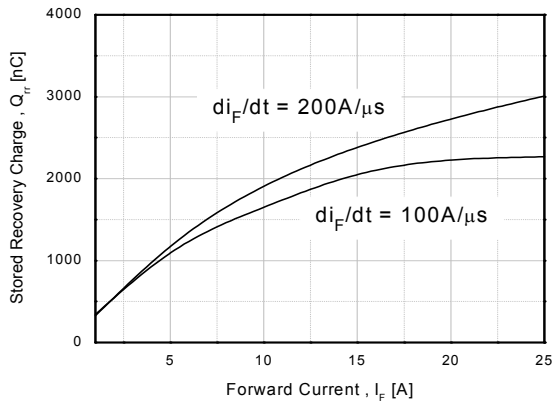
**Figure 18. Forward Characteristics**



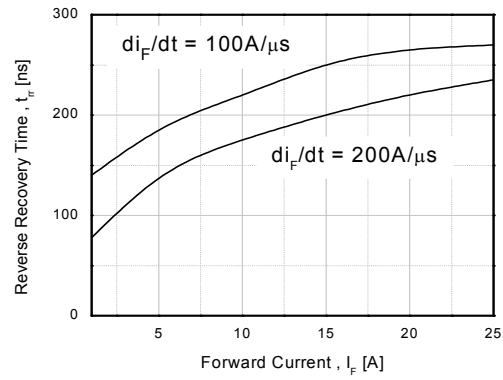
**Figure 19. Reverse Recovery Current**



**Figure 20. Stored Charge**

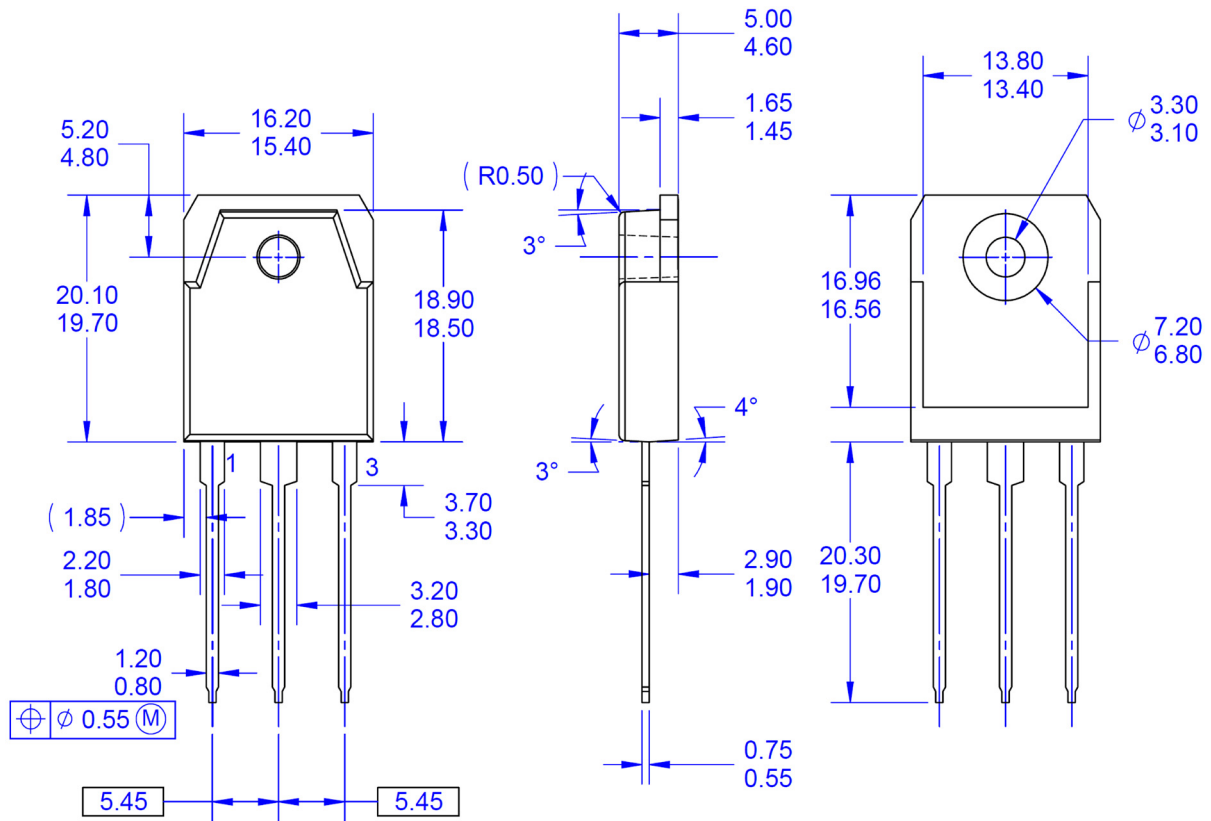


**Figure 21. Reverse Recovery Time**



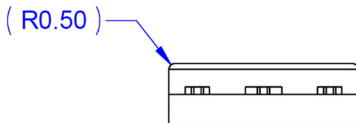


**Mechanical Dimensions**



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.



**Figure 22. TO3PN, 3-Lead, Plastic, EIAJ SC-65**

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